

<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> Form PTO-1449 (Modified) (Use several sheets if necessary)				<b>COMPLETE IF KNOWN</b>	
				Application Number	10/782,564
				Confirmation Number	
				Filing Date	02/18/04
				First Named Inventor	Jack Zezhong Peng
				Group Art Unit	2827
Examiner Name	Huan Hoang				
Attorney Docket No.	384848013US1				
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U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No.	U.S. Patent or Application		Name of Patentee or Inventor of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		NUMBER	Kind Code (if known)			
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		Office	NUMBER	Kind Code (if known)				
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OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume issue number(s), publisher, city and/or country where published.		T
HU		MIRANDA, ENRIQUE et al; Analytic Modeling of Leakage Current Through Multiple Breakdown Paths in SiO2 Films; 39 <sup>th</sup> Annual International Reliability Physics Symposium; Orlando, FL 2001.		
		LOMBARDO; S. et al; Softening of Breakdown in Ultra-Thin Gate Oxide nMOSFET's at Low Inversion Layer Density; 39 <sup>th</sup> Annual International Reliability Physics Symposium; Orlando, FL 2001.		
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<i>HH</i>		DeGRAAF, C., et al, A Novel High-Density Low-Cost Diode Programmable Read Only Memory, IEEE, 1998.	

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